RF Power Field Effect Transistors

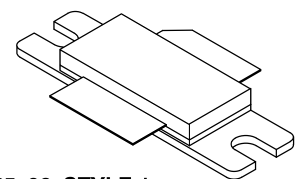
N-Channel Enhancement-Mode Lateral MOSFETs

MRF6S21100HR3
MRF6S21100HSR3

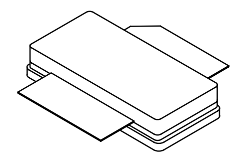
Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

- Typical 2-carrier W-CDMA Performance for V_{DD} = 28 Volts, I_{DQ} = 950 mA, P_{out} = 23 Watts Avg., Full Frequency Band, Channel Bandwidth = 3.84 MHz, Peak/Avg. = 8.5 dB @ 0.01% Probability on CCDF.
  Power Gain — 15.9 dB
  Drain Efficiency — 27.6%
  IM3 @ 10 MHz Offset — -37 dBc @ 3.84 MHz Channel Bandwidth
  ACPR @ 5 MHz Offset — -39.5 dBc @ 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2140 MHz, 100 Watts CW Output Power
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched, Controlled Q, for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- Low Gold Plating Thickness on Leads, 40μ″ Nominal.
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

2170 MHz, 23 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF6S21100HR3



CASE 465A-06, STYLE 1
NI-780S
MRF6S21100HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	388 2.2	W W/°C
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1)	Unit
Thermal Resistance, Junction to Case Case Temperature 80°C, 100 W CW Case Temperature 77°C, 23 W CW	$R_{\theta JC}$	 0.45 0.52	°C/W

1. Refer to AN1955/D, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.freescale.com/rf. Select Documentation/Application Notes - AN1955.

NOTE - **CAUTION** - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114-G)	3A (Minimum)
Machine Model (per EIA/JESD22-A115-A)	A (Minimum)
Charge Device Model (per JESD22-C101-A)	IV (Minimum)

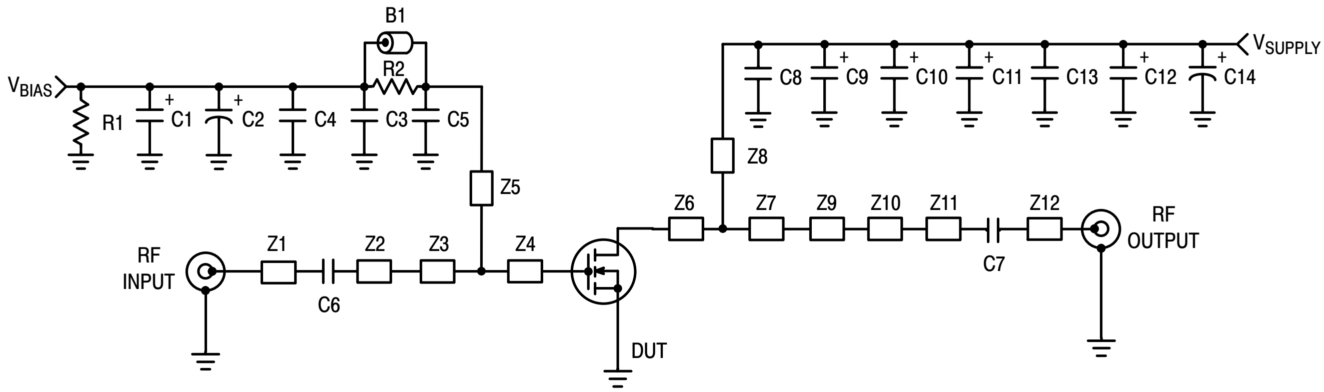
Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current (V_{DS} = 68 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 200 μAdc)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage (V_{DS} = 28 Vdc, I_D = 950 mAdc)	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage (V_{GS} = 10 Vdc, I_D = 2.2 Adc)	$V_{DS(on)}$	—	0.21	0.3	Vdc
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 2 Adc)	g_{fs}	—	5.3	—	S
Dynamic Characteristics (1)					
Reverse Transfer Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	1.5	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 950 mA, P_{out} = 23 W Avg., f1 = 2112.5 MHz, f2 = 2122.5 MHz and f1 = 2157.5 MHz, f2 = 2167.5 MHz, 2-carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers, ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset. IM3 measured in 3.84 MHz Channel Bandwidth @ ±10 MHz Offset. Peak/Avg. = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	15	15.9	17	dB
Drain Efficiency	η_D	26	27.6	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-39.5	-38	dBc
Input Return Loss	IRL	—	-16	-9	dB

1. Part is internally matched both on input and output.



Z1, Z12	1.250″ x 0.084″ Microstrip	Z7	0.320″ x 0.880″ Microstrip
Z2	1.070″ x 0.084″ Microstrip	Z8	0.120″ x 0.820″ Microstrip
Z3	0.330″ x 0.800″ Microstrip	Z9	0.035″ x 0.320″ Microstrip
Z4	0.093″ x 0.800″ Microstrip	Z10	0.335″ x 0.200″ Microstrip
Z5	1.255″ x 0.040″ Microstrip	Z11	0.650″ x 0.084″ Microstrip
Z6	0.160″ x 0.880″ Microstrip	PCB	Arlon GX-0300-55-22, 0.030″, ε_r = 2.55

Figure 1. MRF6S21100HR3(SR3) Test Circuit Schematic

Table 5. MRF6S21100HR3(SR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Ferrite Bead	2743019447	Fair-Rite
C1	1.0 μF, 50 V Tantalum Capacitor	T491C105M050	Kemet
C2	10 μF, 50 V Electrolytic Capacitor	EEV-HB1H100P	Panasonic
C3	1000 pF 100B Chip Capacitor	100B102JCA500X	ATC
C4, C13	0.1 μF 100B Chip Capacitors	CDR33BX104AKWS	Kemet
C5	5.1 pF Chip Capacitor	100B5R1JCA500X	ATC
C6, C7	15 pF Chip Capacitors	100B150JCA500X	ATC
C8	6.8 pF Chip Capacitors	100B6R8JCA500X	ATC
C9, C10, C11, C12	22 μF, 35 V Tantalum Capacitors	T491X226K035AS4394	Kemet
C14	100 μF, 50 V Electrolytic Capacitor	515D107M050BB6A	Vishay/Sprague
R1	1.0 kΩ, 1/8 W Chip Resistor		
R2	10 Ω, 1/8 W Chip Resistor		

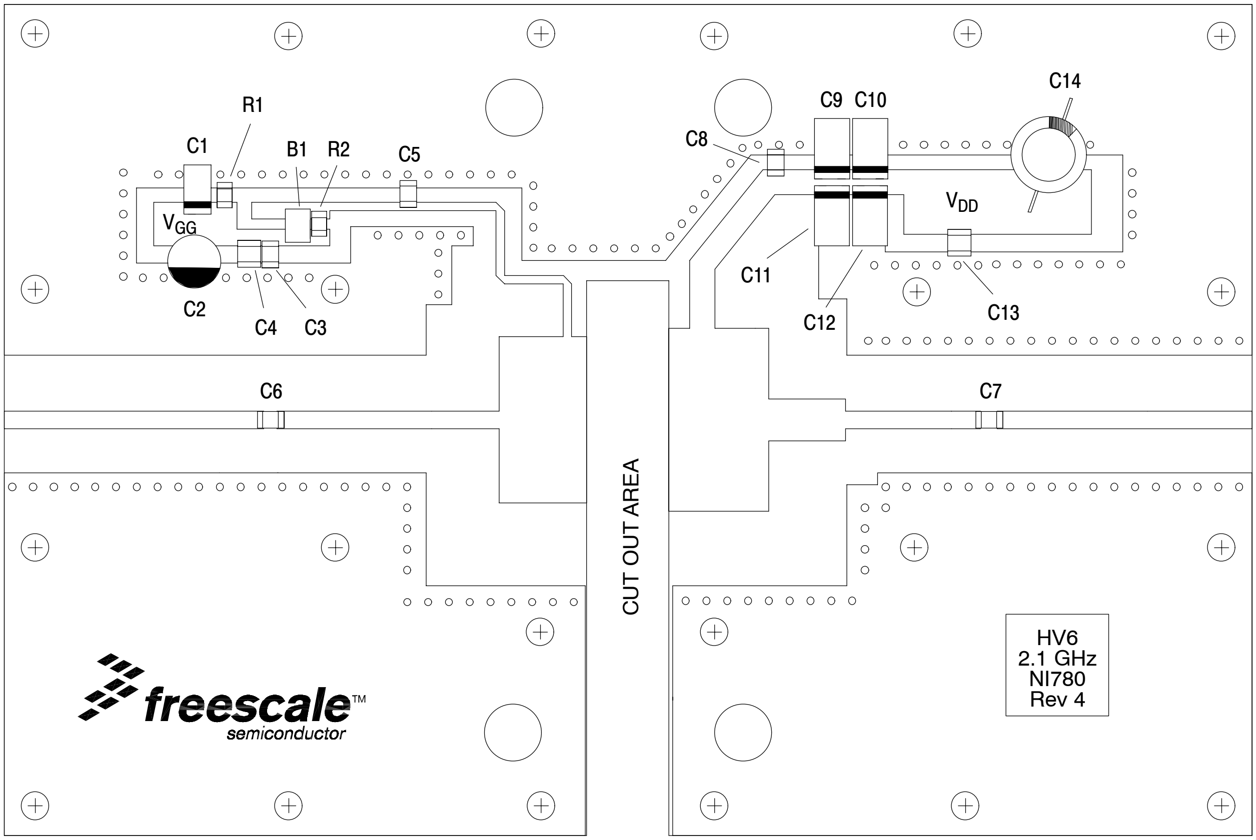


Figure 2. MRF6S21100HR3(SR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

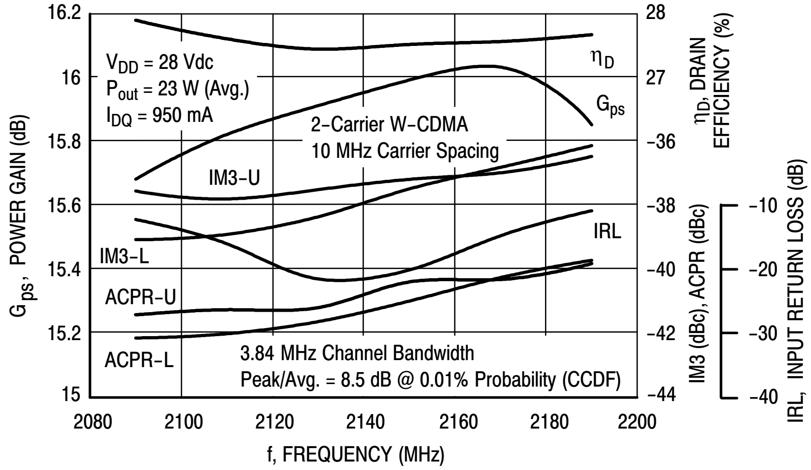


Figure 3. 2-Carrier W-CDMA Broadband Performance

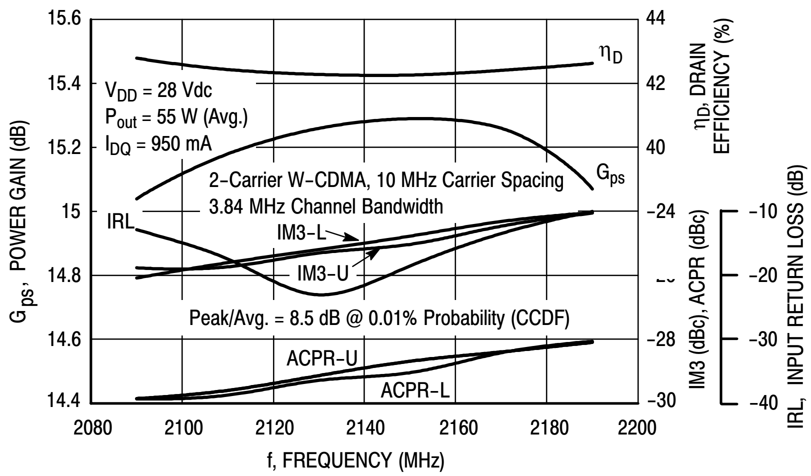


Figure 4. 2-Carrier W-CDMA Broadband Performance

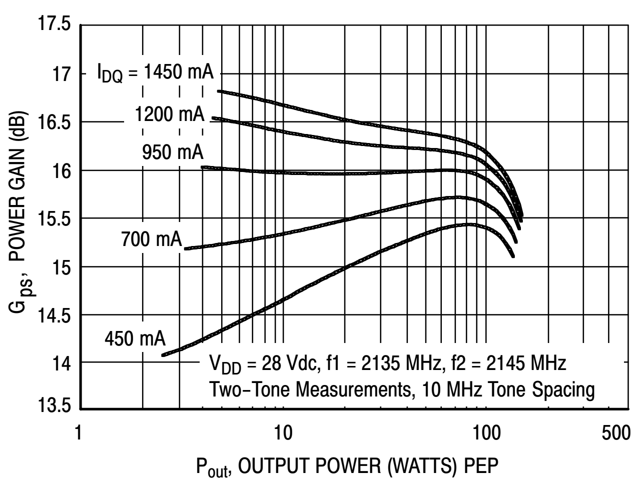


Figure 5. Two-Tone Power Gain versus Output Power

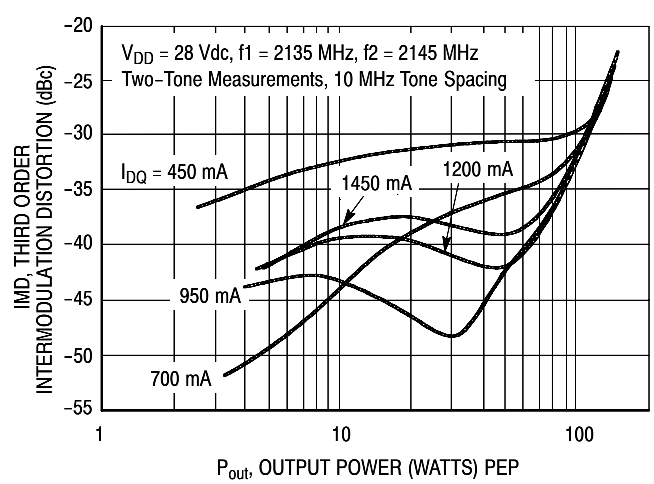


Figure 6. Third Order Intermodulation Distortion versus Output Power

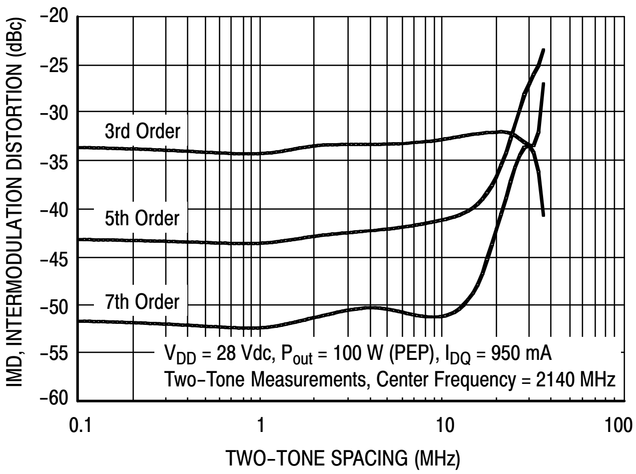


Figure 7. Intermodulation Distortion Products versus Tone Spacing

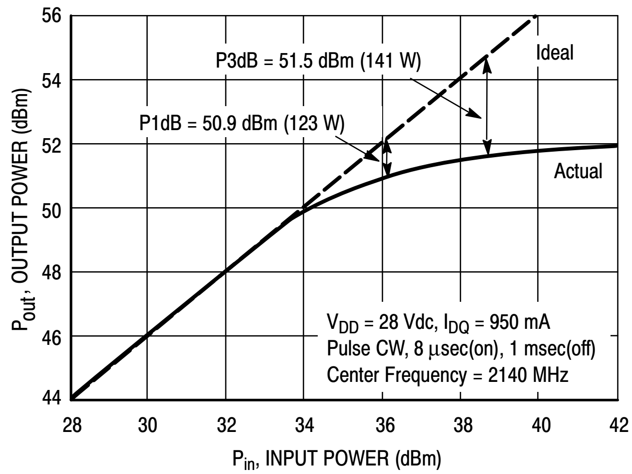


Figure 8. Pulse CW Output Power versus Input Power

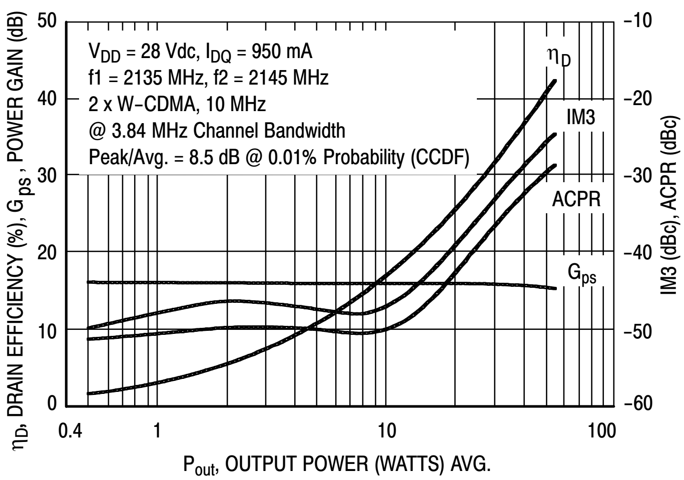


Figure 9. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

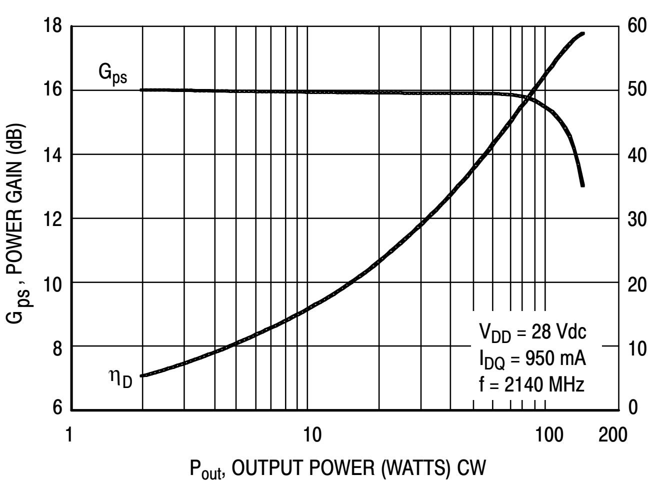


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

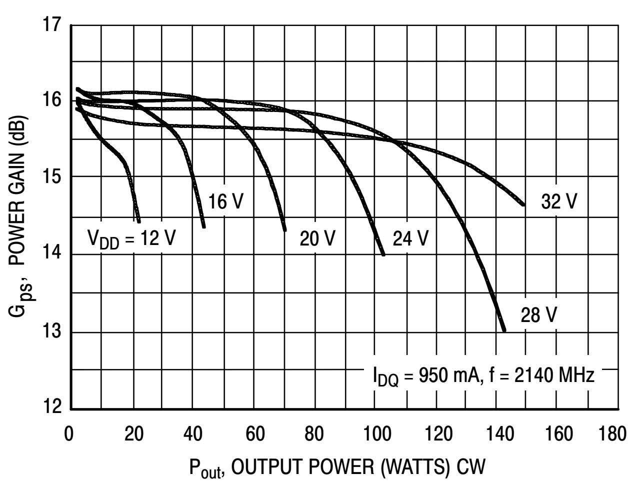
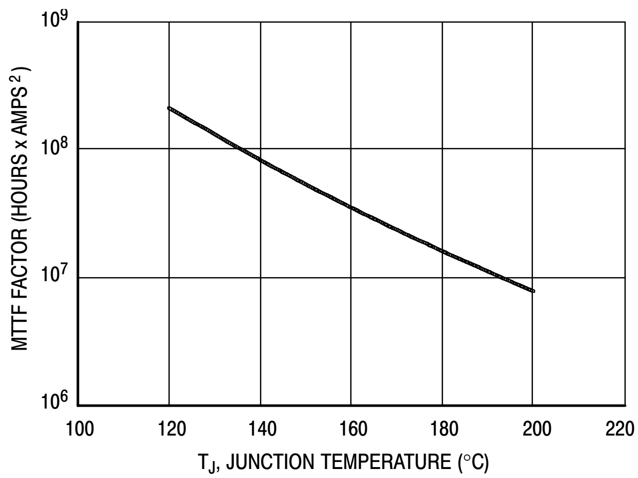


Figure 11. Power Gain versus Output Power

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere^2 drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 12. MTTF Factor versus Junction Temperature

TYPICAL CHARACTERISTICS
W-CDMA TEST SIGNAL

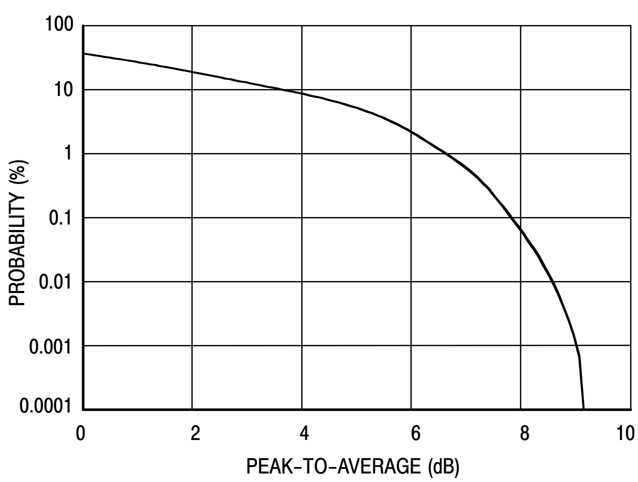


Figure 13. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

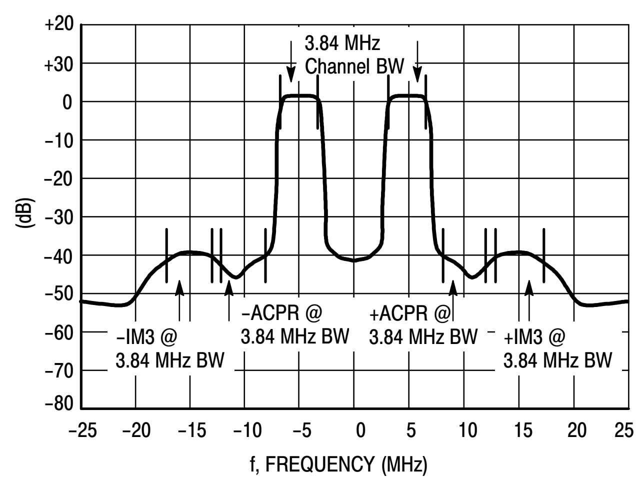
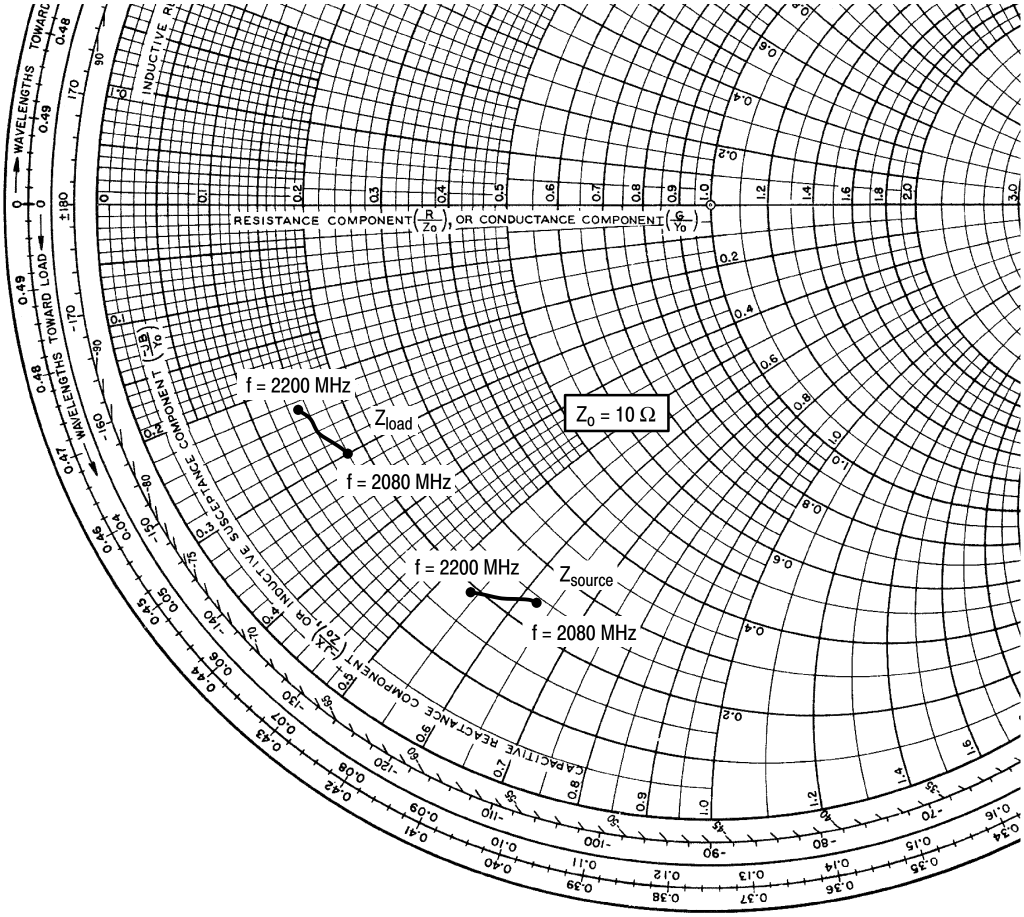


Figure 14. 2-Carrier W-CDMA Spectrum



V_{DD} = 28 Vdc, I_{DQ} = 950 mA, P_{out} = 23 W Avg.

f MHz	Z_{source} Ω	Z_{load} Ω
2080	2.44 - j6.3	1.83 - j3.0
2110	2.25 - j6.1	1.74 - j2.8
2140	2.09 - j5.8	1.61 - j2.6
2170	1.98 - j5.6	1.59 - j2.5
2200	1.85 - j5.4	1.52 - j2.3

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

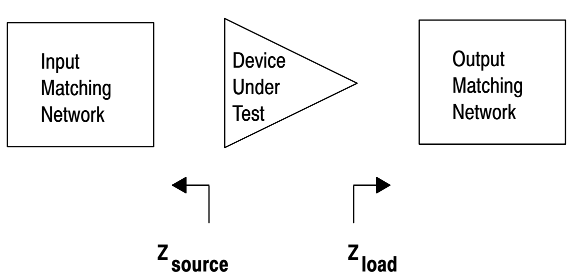
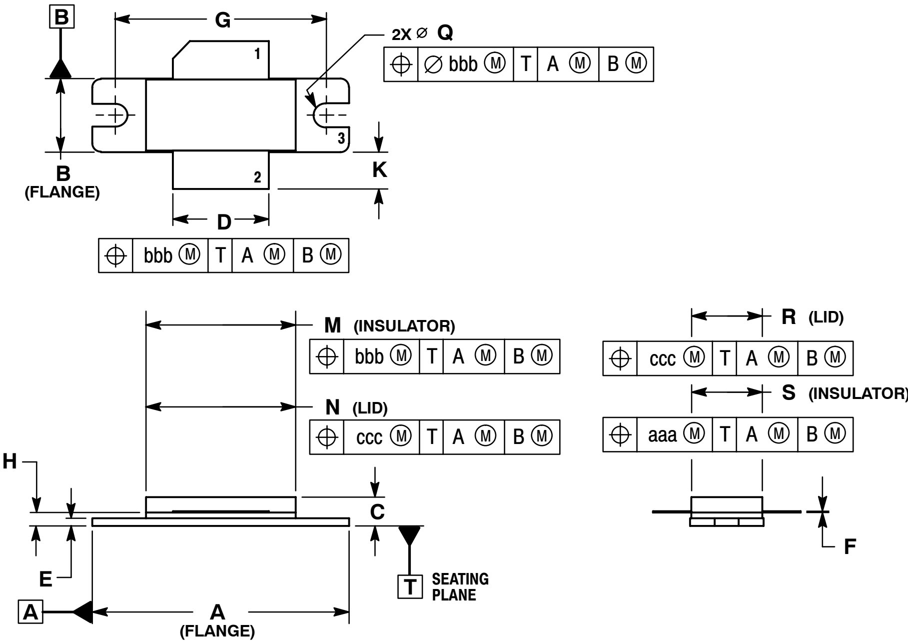


Figure 15. Series Equivalent Source and Load Impedance

NOTES

NOTES

PACKAGE DIMENSIONS

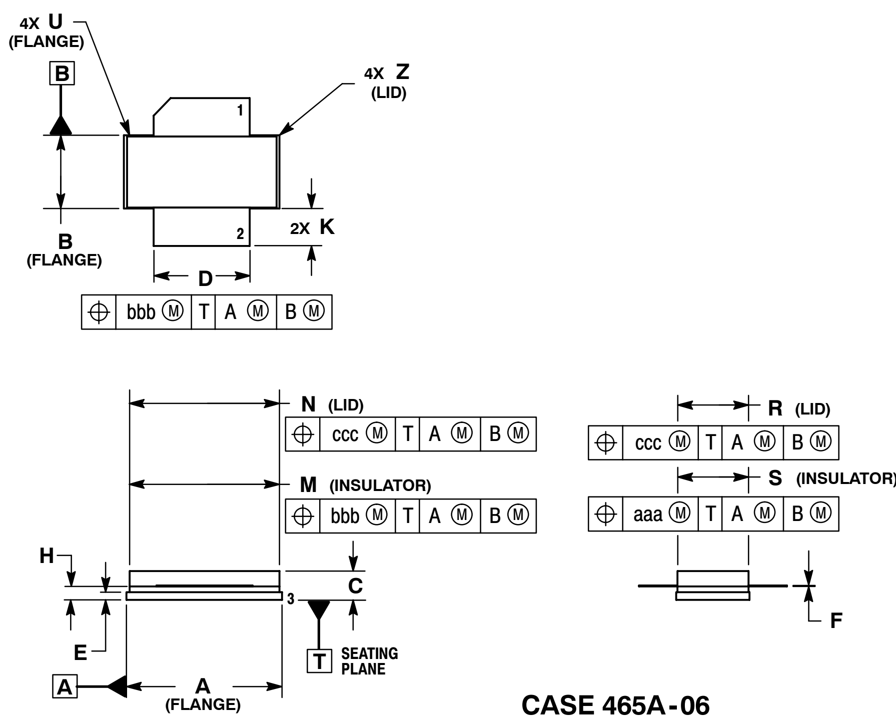


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M−1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	∅.118	∅.138	∅3.00	∅3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465-06
ISSUE F
NI-780
MRF6S21100HR3



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3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
5. SOURCE

CASE 465A-06
ISSUE F
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